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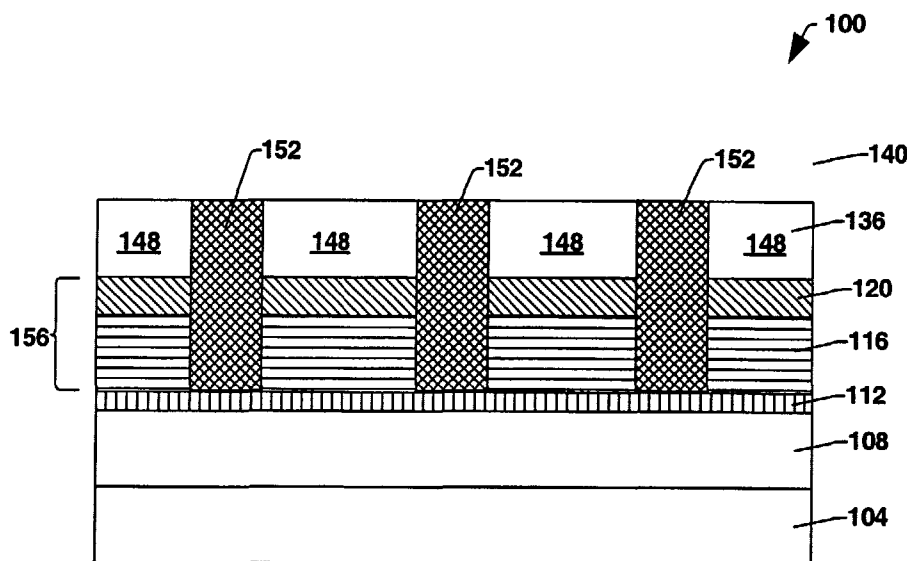
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(54) Title: SELF ALIGNED MEMORY ELEMENT AND WORDLINE



(57) Abstract: An organic polymer memory cell is provided having an organic polymer layer (116, 2108, 2132, 2168) and an electrode layer (120, 2112, 2128, 2164) formed over a first conductive (e.g., copper) layer (e.g., bitline) (104, 108). The memory cells are connected to a second conductive layer (e.g., forming a wordline) (136, 2148, 2160), and more particularly the top of the electrode layer of the memory cells to the second conductive layer. Optionally, a conductivity facilitating layer (112, 2136) is formed over the conductive layer. Dielectric material separates the memory cells. The memory cells are self-aligned with the bitlines formed in the first conductive layer and the wordlines formed in the second conductive layer.

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